

Application Serial No. 10/555,141
Amendment dated October 16, 2006
Reply to Office Action dated July 12, 2006

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously presented): A method for texturing surfaces of silicon wafers comprising the steps of dipping said silicon wafers in an etching solution of water, concentrated hydrofluoric acid and concentrated nitric acid and setting a temperature for the etching solution, wherein said etching solution consists essentially of, in percent, 20% to 55% water, 10% to 40% concentrated hydrofluoric acid and 20% to 60% concentrated nitric acid and the temperature of said etching solution is between 0 and 15 degrees Celsius.

Claim 2 (previously presented): The method as in claim 1, wherein said etching solution consists essentially of, in percent, 30% to 40% water, 15% to 30% concentrated hydrofluoric acid and 30% to 50% concentrated nitric acid.

Claim 3 (previously presented): The method as in claim 1, wherein the temperature of said etching solution is between 7 and 9 degrees Celsius.

Claim 4 (previously presented): The method as in claim 1, wherein said silicon wafers remain in said etching solution for between 3 and 5 minutes.

Claim 5 (previously presented): The method as in claim 1, wherein said etching solution consists essentially of, in percent, 31% water, 23% concentrated hydrofluoric acid and 46% concentrated nitric acid, in that the temperature of said etching solution is 8 degrees Celsius, and said silicon wafers remain in said etching solution for between 1.5 and 2 minutes.

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Claim 6 (previously presented): The method as in claim 1, wherein said silicon wafers are oriented substantially vertically and said etching solution has a flow component.

Claim 7 (previously presented): The method as in claim 1, wherein said silicon wafers are oriented substantially horizontally and said etching solution is quiescent.

Claim 8 (previously presented): The method as in claim 7, wherein said silicon wafers are moved through said etching solution.

Claim 9 (previously presented): The method as in claim 1, wherein said silicon wafers are polycrystalline.